

General Description

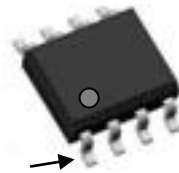
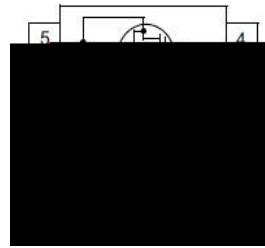
The ZMD68603S combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Features

- Trench technology
- $R_{DS(ON)}$ to minimize conductive loss
- fast switching
- Dual DIE in one package

Application

Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems

Product Summary

Ordering Information:

Part NO.	ZMD68603S
Marking	ZMD68603
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	4.5	A
	$I_{D@TC=75}$	3.4	A
	$I_{D@TC=100}$	2.8	A
Pulsed Drain Current	I_{DM}	12	A
Total Power Dissipation	$P_D@TC=25$	3.6	W
Total Power Dissipation	$P_D@TA=25$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	25	mJ

Fig.1 Power Dissipation

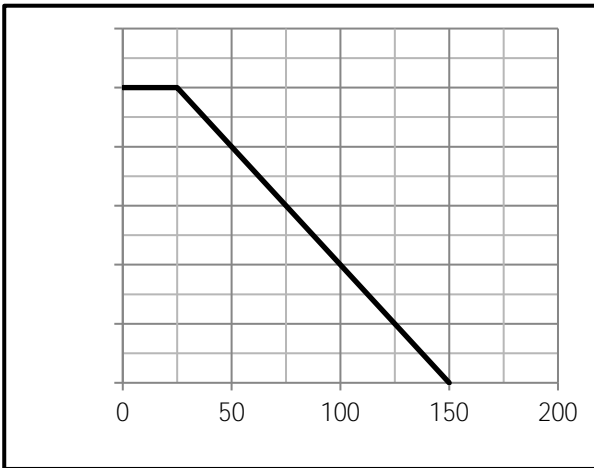


Fig.2 Typical output Characteristics

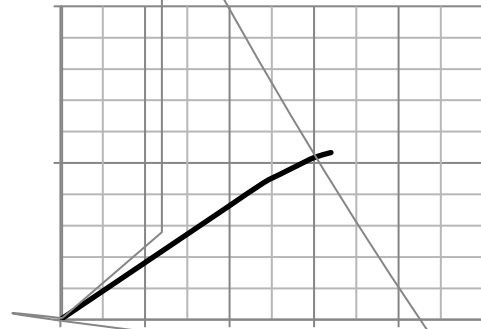


Fig.3 Threshold Voltage V.S Junction Temperature

Fig.4 Resistance V.S Drain Current



Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

